

REMARKS***Claim Rejections Under 35 U.S.C. § 112***

Claims 1-6 and 9 were rejected under 35 U.S.C. §112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claim 1 has been amended to overcome the rejection under 35 U.S.C. § 112, second paragraph.

Claim Rejections Under 35 U.S.C. § 103

Claims 1-6, 9, 11-12, 14-15, 17, 19-22 were rejected under 35 U.S.C. § 103(a) as being unpatentable over *Chang et al.* (U.S. Patent No. 6,486,028 B1, previously cited by Applicants). Applicants respectfully traverse this rejection.

Chang et al. disclose a method for fabricating a nitride read only memory cell as a vertical structure. The structure of *Chang et al.* forms the ONO throughout the entire trench, both sides and bottom. This is not the same as what is claimed by Applicants in the presently amended claims.

Applicants' amended claims are to a memory array that has an ONO structure only on the sidewalls of the non-horizontal or vertical edge surfaces. Additionally, an oxide layer of the ONO structure that is along each sidewall is thicker only in one portion that is adjacent to the first region. These elements are neither taught nor suggested by *Chang et al.*

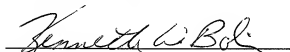
CONCLUSION

In view of the above remarks, Applicant believes that all pending claims are in condition for allowance and respectfully requests a Notice of Allowance be issued in this case. Please charge any further fees deemed necessary or credit any overpayment to Deposit Account No. 501373.

If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Respectfully submitted,

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